

**ECE 3214: Semiconductor Device Fundamentals**  
**VIRGINIA TECH**  
**Course Syllabus (CRN 83119 )**  
**Fall 2019 TR 2:00-3:15 PM**

**I. ECE 3214 SEMICONDUCTOR DEVICE FUNDAMENTALS**

**Instructor:** Prof. Mantu Hudait, Dept. of ECE, 626 Whittemore Hall  
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**Class Room:** **RAND 318**

<b>Final Exam date and time</b>	Exam Date: <b>December 17<sup>th</sup>, 2019</b>	<b>Midterm-I (in class)</b>	<b>September 26<sup>th</sup></b>
	Begin Time: 2:05 PM	<b>Midterm-II (in class)</b>	<b>October 31<sup>th</sup></b>
<b>Office Hours:</b>	End Time: 4:05 PM	<b>Final (in class room)</b>	<b>December 17<sup>th</sup>, 2019</b>

**Tuesday: 10:00 am-12:00 pm** and by appointment (e-mail please).

**Course Description:**

The course will cover the device physics and device applications: Fundamental semiconductor device physics associated with semiconductor devices and in-depth understanding of p/n junction diodes, bipolar junction transistors, MOS capacitor, and junction field effect transistors.

**Learning Objectives:**

Having successfully completed 3214, students will be able to:

- Determine the band structure of semiconductors when supplied with basic materials properties and applying their knowledge of quantum mechanics.
- Calculate carrier distributions in thermal equilibrium and non-thermal equilibrium conditions for intrinsic and doped semiconductors.
- Apply basic semiconductor drift-diffusion equations to determine current flow in semiconductor devices.
- Differentiate between the fundamental difference of p/n junctions and field effect transistors
- Determine alignment of metal-semiconductor band diagrams and identify whether junction is Ohmic or Schottky.
- Design a bipolar transistor, metal-oxide-semiconductor and/or a field effect transistor that meet specific performance criteria through the selection of the appropriate semiconductor material(s), doping, and device dimensions.

**II. PREREQUISITES & COREQUISITES**

**Prerequisites:** 2204 or MSE 3204 or PHYS 3455 (**MUST**).

The student will be introduced briefly the fundamentals of quantum mechanics. But some prior knowledge of this topic and solid-state physics will also help.

### **III. TEXTS AND SPECIAL TEACHING AIDS**

#### **Required Text**

**D.A. Neamen, *Semiconductor Physics & Devices*, 4<sup>th</sup> ed., McGraw-Hill, 2012; Hardcover, 768 pages ©2012, ISBN-13 978-0-07-352958-5.**

#### **Additional Reference Books:**

- Umesh Mishra and Jasprit Singh, *Semiconductor Device Physics and Design*, Springer, 2008 (e-book available through [www.lib.vt.edu](http://www.lib.vt.edu))
- M. Shur, *Physics of Semiconductor Devices*, Englewood Cliffs, NJ: Prentice Hall, 1990.

### **IV. EDUCATIONAL OBJECTIVES**

The lecture sessions provides learning opportunities that should enable you to do the following upon completion of this course:

**A.** Develop a basic understanding on the following key concepts in quantum and statistical mechanics relevant to physical properties of electronic materials and their device applications:

#### ***i. Quantum Mechanics:***

Crystal structure of solids; space lattices; wave particle duality; Schrodinger's wave equation; particle trapped in a box; particle tunneling through a barrier; allowed and forbidden energy bands; propagating electron wave in a periodic lattice; effective mass; density of states; strain effect on band structure; quantization effects in nanoscale devices

#### ***ii. Statistical Mechanics:***

The Fermi-Dirac and Maxwell-Boltzmann probability distribution function; the Fermi energy;

#### ***iii. Equilibrium vs non-equilibrium properties:***

Carrier distribution at equilibrium; doped semiconductors; compensated semiconductor; carrier transport phenomena; hall effect; excess carriers in semiconductors; continuity equation; Poisson's equation.

#### ***iv. p-n junction:***

Carrier distribution and field profile at a p-n junction; diode I-V characteristics and non-idealities, diode capacitance, heterostructures, band alignment; quantum well properties.

#### ***v. MOS capacitors and field effect transistors:***

Understand and interpret C-V characteristics; understand the physical structure and detailed operation of Metal-Oxide Semiconductor Field-Effect Transistors (MOSFETs); understand the terminal I-V characteristics of MOSFETs and their associated non-idealities due to scaling; high electron mobility transistors; tunnel transistors; FinFETs.

#### ***vi. Bipolar junction transistors:***

Understand the physical operation of solar cell and its efficiency limits; heterojunctions to improve efficiency; potential impact on global energy crisis and light emitting diodes.

#### ***vii. Solar cells and optical devices***

Carrier recombination and lifetime; carrier transport of p-n junction under illumination; solar cell parameters and device design; III-V heterojunctions single and multijunction solar cells; tailor-made bandgaps for matching solar spectrum.

*Generation of light:* light emitting diodes and semiconductor lasers. *Detection of light:* Solid state detectors

**B.** Become proficient with the fundamental device physics concepts

**C.** Learn to analyze device characteristics in detail and brainstorm ways towards improving them or adapting them to new applications

## V. SYLLABUS

### Section 1

Topic	Number of Lectures ( <b>Tentative</b> )
1. Crystalline Structures	2
2. Basic Quantum Mechanics and Bandgaps	2
3. Band Diagrams	1
4. Carrier Concentration and Fermi Level	2
5. Drift-diffusion and Carrier Mobility	2
6. Recombination and Generation of Carriers	1
7. Measurement of Resistivity and Mobility	Reading Materials

### **Midterm Exam 1 (September 20<sup>th</sup>)**

#### Section 2

1. p-n Diodes	3
2. Schottky Diodes and Ohmic Contacts	1
3. Heterostructures	2
4. Bipolar Transistors	2

### **Midterm Exam 2 (October 31<sup>st</sup>)**

#### Section 3

1. MOSFETs, Quantum well FETs, FinFETs	4
2. Tunnel FETs	1
3. Solar cells and optical devices	4

## Final Exam (cover all chapters)

## VI. GRADING POLICY

<b>Homework</b>	<b>10%</b>
<b>Midterm-I</b>	<b>20%</b>
<b>Midterm-II</b>	<b>30%</b>
<b>Final (all chapters)</b>	<b>40%</b>
<b>Total</b>	<b>100%</b>

### Home Work (Please Read): (10%)

Homework problems will be typically be assigned on a weekly basis and will be due at the end of class one week following its assignment. **No assignments will be accepted after the solution is posted**, except in the case of unforeseen, officially documented absences. The solution will be posted the day homework is due. No electronic submission of homework and it should be submitted in the class.

Each problem solution should be **neatly worked out**. If a given assignment requires multiple pages of work, it must be stapled together prior to submission. Use neatly trimmed 8.5" x 11" paper and write on one side only. When possible, sketch illustrative diagrams and label current, voltage, and other relevant quantities on the diagrams. Very rough sketches with no labels will receive no credit. Use industrially accepted notation for units, per discussion on Day 1 of class.

I will collect ALL assigned problems for grading. However, all problems may not necessarily be graded. I expect you to have worked ALL the problems and to be prepared to submit the problem solutions in the above format at the end of class on the date due.

You may consult with other students and with your instructor while you are working on assigned problems but your goal in consulting should be limited to exploring options and approaches rather than avoiding work. The ability to solve problems develops through disciplined effort and the exams will require you to be able to solve problems. To obtain full credit for a homework assignment you must submit it to your instructor in class on the due date. Note that if you use open source solution for your homework, you will have a difficulty to answer questions in either midterm or final exam. I usually ask questions during class and your participation is most important.

#### **Attendance: (0%)**

**Attendance all lecture classes is expected and critical to your successfully completing the requirements of this course.** I will periodically check attendance against the class roll and you will have only 3 missing classes due to unforeseen, officially documented absences without any penalties. However, chronic absenteeism will be noted, and I will not be inclined to give such individuals the benefit of the doubt in judgment situations such as borderline final grades. In the event that you miss a lecture, it is your responsibility to ask one of your classmates or read text book. If you have a conflict with a scheduled exam, you must make arrangements with your instructor well in advance so that alternate times can be scheduled.

#### **Exams (Please read): (90% = 20%+30%+40%)**

**There will be only 2 mid-term exams and one final exam (September 26<sup>th</sup> for Midterm-I; October 31<sup>st</sup>**

**Midterm-II; December 17<sup>th</sup> Final all in class room RAND 318). No make-up exams will be given except for unforeseen, officially documented absences.** If such a circumstance arises on a test date, it is your responsibility to contact me as soon as possible. If you expect to be absent on a test date for any legitimate reason (conferences, job interviews, project team competitions, etc.), it is your responsibility to give me sufficient prior notice so that we can make other arrangements. There will be a **FINAL exam** at the end of this course (**Cumulative**).

## **VII. ACADEMIC INTEGRITY**

The Virginia Tech Honor Code establishes the standard for **ACADEMIC INTEGRITY** in this course, and will be strictly enforced. *Discussion* of class material with your classmates or the instructor is encouraged; however, ALL submitted work, must represent your own efforts, and you must pledge to this effect on all work. For more details on the relevant honor codes, consult the websites listed below:

- [Undergraduate Honor System, http://www.honorsystem.vt.edu/index.html](http://www.honorsystem.vt.edu/index.html)

#### **Honor Code Pledge for Assignments:**

**The Undergraduate Honor Code pledge that each member of the university community agrees to abide by states:**

**“As a Hokie, I will conduct myself with honor and integrity at all times. I will not lie, cheat, or steal, nor will I accept the actions of those who do.”**

Students enrolled in this course are responsible for abiding by the Honor Code. A student who has doubts about how the Honor Code applies to any assignment is responsible for obtaining specific guidance from the course instructor before submitting the assignment for evaluation. Ignorance of the rules does not exclude any member of the University community from the requirements and expectations of the Honor Code. For additional information about the Honor Code, please visit:

- <https://www.honorsystem.vt.edu/>
- All assignments submitted shall be considered "graded work" and all aspects of your coursework are covered by the Honor Code. All projects and homework assignments are to be completed individually unless otherwise specified.
- Commission of any of the following acts shall constitute academic misconduct. This listing is not, however, exclusive of other acts that may reasonably be said to constitute academic misconduct. Clarification is provided for each definition with some examples of prohibited behaviors in the Undergraduate Honor Code Manual located at <https://www.honorsystem.vt.edu/>

#### **A. CHEATING**

- Cheating includes the intentional use of unauthorized materials, information, notes, study aids or other devices or materials in any academic exercise, or attempts thereof.

#### **B. PLAGIARISM**

- Plagiarism includes the copying of the language, structure, programming, computer code, ideas, and/or thoughts of another and passing off the same as one's own original work, or attempts thereof.

#### **C. FALSIFICATION**

- Falsification includes the statement of any untruth, either verbally or in writing, with respect to any element of one's academic work, or attempts thereof.

#### **D. FABRICATION**

- Fabrication includes making up data and results, and recording or reporting them, or submitting fabricated documents, or attempts thereof.

#### **E. MULTIPLE SUBMISSION**

- Multiple submission involves the submission for credit—without authorization of the instructor receiving the work—of substantial portions of any work (including oral reports) previously submitted for credit at any academic institution, or attempts thereof.

#### **F. COMPLICITY**

- Complicity includes intentionally helping another to engage in an act of academic misconduct, or attempts thereof.

#### **G. VIOLATION OF UNIVERSITY, COLLEGE, DEPARTMENTAL, PROGRAM, COURSE, OR FACULTY RULES**

- The violation of any University, College, Departmental, Program, Course, or Faculty Rules relating to academic matters that may lead to an unfair academic advantage by the student violating the rule(s).

#### **Academic Misconduct Sanctions:**

“If you have questions or are unclear about what constitutes academic misconduct on an assignment, please speak with me. I take the Honor Code very seriously in this course. The normal sanction I will recommend for a violation of the Honor Code is an **F\*** sanction as your final course grade. The F represents failure in the course. The “\*” is intended to identify a student who has failed to uphold the values of academic integrity at Virginia Tech. A student who receives a sanction of **F\*** as their final course grade shall have it documented on their transcript with the notation “FAILURE DUE TO ACADEMIC HONOR CODE VIOLATION.” You would be required to complete an education program administered by the Honor System in order to have the “\*” and notation “FAILURE DUE TO ACADEMIC HONOR CODE VIOLATION” removed from your transcript. The “F” however would be permanently on your transcript.”

### **VIII. SPECIAL AID STUDENTS:**

You must work through our SSD center and your all exams will be supervised by them. You can't give one exam at SSD center and other exam at your class room. I must need to follow the school policy. You need to sign your special aid paper as soon as possible. Due to large number of incoming students, you also must work with me so that SSD center room **MUST** be reserved. It's your responsibility to get the paper work done and I need to only reserve the room for you.

### **IX. ANNOUNCEMENTS**

I will use Canvas to post homework assignments, homework solutions, and other information pertaining to the course materials. You should check your email and the Canvas on a regular basis. In case, I use any teaching materials not from the text book, I will post **only those lecture notes** in Canvas. Lecture notes I prepared for enhancement you participation in class. *You need to read the text book prior to class or after the class, please!*

#### **Read Chapters for this course:**

***Chapter-1: pages 1-20 (exercise: 21-24)***

***Chapter-2: pages 25-52 (exercise: 52-57)***

***Chapter-3: pages 58-100 (exercise: 100-104)***

***Chapter-4: pages 106-149 (exercise: 149-154)***

***Chapter-5: pages 156-1840 (exercise: 184-191)***

***Chapter-6: pages 192-201 (exercise: 233-240)***

***Chapter-7: pages 241-262 (exercise: 269-274)***

***Chapter-8: pages 276-295 (exercise: 323-330)***

***Chapter-9: pages 331-364 (exercise: 365-370)***

***Chapter-10: pages 371-419 (exercise: 433-441)***

***Chapter-12: pages 491-521 (exercise: 560-565)***

***Chapter-14: pages 618-639, 648-662 (exercise: 663-668)***